

Specification	Products	Type
		RXT2907A

1. SCOPE RXT2907A

1.1 Scope. This specification covers the detail requirements for one type PNP silicon epitaxial planar transistor designed for audio frequency small signal amplifier.

1.2 Physical dimensions. See figure 1.

1.3 Absolute maximum ratings. ($T_a=25\text{ }^\circ\text{C}$)

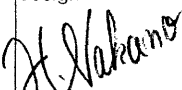
Collector to base voltage	V_{CBO}	-60V
Collector to emitter voltage	V_{CEO}	-60V
Emitter to base voltage	V_{EBO}	-5V
Collector current	I_C	-600mA
Power dissipation	P_C	500mW
Junction temperature	T_j	150 $^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150 $^\circ\text{C}$

2. Electrical characteristics ($T_a=25\text{ }^\circ\text{C}$)

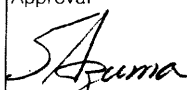
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV_{CBO}	$I_C=-10\text{ }\mu\text{A}$	-60	-	-	V
BV_{CEO}	$I_C=-10\text{ mA}$	-60	-	-	V
BV_{EBO}	$I_E=-10\text{ }\mu\text{A}$	-5	-	-	V
I_{CBO}	$V_{CB}=-50\text{ V}$	-	-	-100	nA
I_{CES}	$V_{CE}=-30\text{ V}$	-	-	-100	nA
I_{EBO}	$V_{EB}=-3\text{ V}$	-	-	-100	nA
$V_{CE}(\text{sat})_1$	$I_C=-150\text{ mA}$, $I_B=-15\text{ mA}$	-	-	-0.4	V
$V_{CE}(\text{sat})_2$	$I_C=-500\text{ mA}$, $I_B=-50\text{ mA}$	-	-	-1.6	V
$V_{BE}(\text{sat})_1$	$I_C=-150\text{ mA}$, $I_B=-15\text{ mA}$	-	-	-1.3	V
$V_{BE}(\text{sat})_2$	$I_C=-500\text{ mA}$, $I_B=-50\text{ mA}$	-	-	-2.6	V
$h_{FE} 1$	$V_{CE}=-10\text{ V}$, $I_C=-0.1\text{ mA}$	75	-	-	
$h_{FE} 2$	$V_{CE}=-10\text{ V}$, $I_C=-1\text{ mA}$	100	-	-	
$h_{FE} 3$	$V_{CE}=-10\text{ V}$, $I_C=-10\text{ mA}$	100	-	-	
$h_{FE} 4$	$V_{CE}=-10\text{ V}$, $I_C=-150\text{ mA}$	100	-	300	
$h_{FE} 5$	$V_{CE}=-10\text{ V}$, $I_C=-500\text{ mA}$	50	-	-	
f_T	$V_{CE}=-20\text{ V}$, $I_C=-50\text{ mA}$, $f=100\text{ MHz}$	200	-	-	MHz
C_{ob}	$V_{CB}=-10\text{ V}$, $f=100\text{ KHz}$	-	-	8	pF
C_{ib}	$V_{EB}=-2\text{ V}$, $f=100\text{ KHz}$	-	-	30	pF

ROHM CO., LTD.

Design



Approval



Specification No.

TLRXT2907A-1

Date

9/24/86

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		RXT2907A

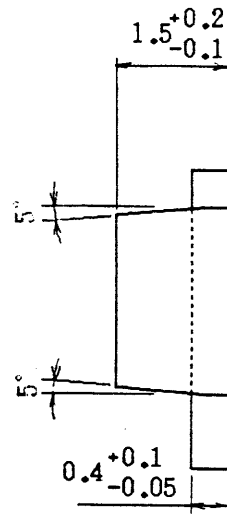
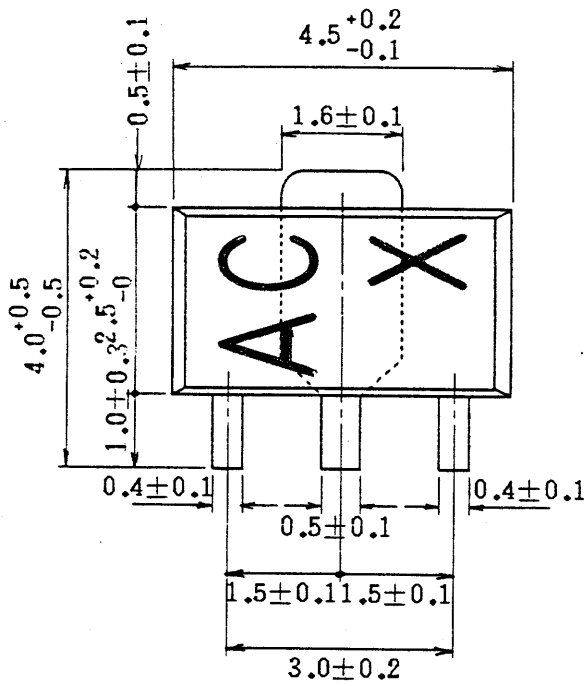
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{on}		—	—	50	nS
t _d	V _{CC} =-30V, V _{BE(OFF)} =-1.5V	—	—	10	nS
t _r	I _C =-150mA, I _{B1} =-15mA	—	—	40	nS
t _{off}		—	—	100	nS
t _s	V _{CC} =-30V, I _C =-150mA	—	—	80	nS
t _f	I _{B1} = I _{B2} =-15mA	—	—	30	nS

Specification

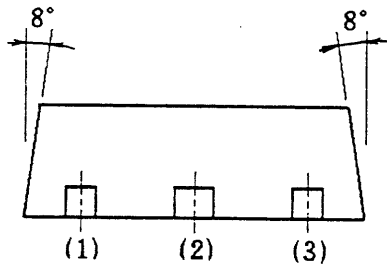
Products

Type

RXT2907A



UNIT: mm



- (1) Base
- (2) Collector
- (3) Emitter

